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ADDED CLAIMS

What is claimed is:

15. (New) A method employed for manufacturing semiconductor devices, comprising:
determining a desired multi-sloped profile;
etching at least one device to conform to the desired multi-sloped profile;
detecting *in situ* parameters of the etching of the device utilizing scatterometry; and
adjusting the etching of the multi-sloped profile as necessary to produce the desired
multi-sloped profile.
16. (New) The method of claim 15, further including storing the desired multi-sloped
profile.
17. (New) The method of claim 15, further including analyzing the parameters of the
etching of the device.
18. (New) The method of claim 17, wherein analyzing includes comparing current
parameters to previous parameters.
19. (New) The method of claim 15, further including storing the parameters found
while detecting *in situ* parameters.
20. (New) The method of claim 15, wherein adjusting the etching of the multi-sloped
profile includes at least one from a group consisting of reducing a rate of etching and
increasing a rate of etching.
21. (New) The method of claim 15, further including controlling light sources utilized
in detecting *in situ* parameters.

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22. (New) The method of claim 21, wherein controlling light sources includes at least one from a group consisting of reducing a light source intensity, increasing a light source intensity and altering an angle of a light source.

23. (New) The method of claim 15, further including controlling light receivers utilized in detecting *in situ* parameters.

24. (New) The method of claim 23, wherein controlling light receivers includes at least one from a group consisting of reducing a light receiver sensitivity, increasing a light receiver sensitivity and altering an angle of a light receiver.

25. (New) A semiconductor device manufacturing system, comprising:
at least one etch component for etching a device to conform to a desired multi-sloped profile;
a detecting system employing scatterometry for detecting *in situ* parameters related to the etching of the device; and
an etch component controller capable of receiving information from the detecting system to control the etch component as necessary to produce the desired multi-sloped profile.

26. (New) The system of claim 25, further comprising an analysis system to analyze *in situ* parameters provided by the detecting system.

27. (New) The system of claim 26, the analysis system additionally analyzes *in situ* parameters based on at least one from a group consisting of current *in situ* parameters, previous *in situ* parameters, scatterometry signature profiles, and predetermined multi-sloped profiles.

28. (New) The system of claim 25, further comprising a storage medium for storing at least one from a group consisting of current *in situ* parameters, previous *in situ* parameters, scatterometry signature profiles, and predetermined multi-sloped profiles.

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29. (New) A system for manufacturing semiconductor devices, comprising:
means for etching at least one device to conform to a desired multi-sloped profile;
means for detecting *in situ* parameters of the etching of the device utilizing
scatterometry; and
means for adjusting the etching of the multi-sloped profile as necessary to produce the
desired multi-sloped profile.

30. (New) A data packet transmitted between two or more components that facilitates
semiconductor device manufacture, the data packet comprising information, based, in part, on
a scatterometry derived means for producing multi-sloped profiled devices.

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